

AMENDMENTS TO THE CLAIMS

1. (Currently amended) A semiconductor light-emitting element mounting member comprising:

a substrate; and

a at least one metal film formed on a surface of said substrate, formed from Ag, Al, or an alloy containing said metals, and functioning as at least one of an electrode layer for mounting at least one of a semiconductor light-emitting element and or a reflective layer for reflecting light from a semiconductor light-emitting element wherein:

the thickness of the at least one metal film is 0.5 - 3 μm ;

crystal grains of said metal or alloy forming said at least one metal film have a particle diameter along a surface plane of said at least one metal film of no more than 0.5 μm ;

said a surface of said metal film has a center-line average roughness Ra of no more than 0.1 μm ;

an adhesion layer and a barrier layer are formed, in sequence, on said substrate, with said metal film being formed on said barrier layer;

the thickness of the adhesion layer is 0.01-1.00 μm ; and

the thickness of the barrier layer is 0.01-1.50 μm .

2. (Canceled)

3. (Previously presented) The semiconductor light-emitting element mounting member according to claim 1 wherein said metal film is formed as an alloy of at least one of Ag and Al and other metal, a proportional content of said other metal being 0.001 - 10 percent by weight.

4. (Previously presented) The semiconductor light-emitting element mounting member according to claim 3 wherein said other metal is at least one type of metal selected from a group consisting of Cu, Mg, Si, Mn, Ti, and Cr.

5. (Canceled)
6. (Previously presented) The semiconductor light-emitting element mounting member according to claim 1 wherein said metal film is formed from Al alone or from an alloy of Al and other metal.
7. (Previously presented) The semiconductor light-emitting element mounting member according to claim 1 wherein a thermal expansion coefficient of said substrate is $1 \times 10^{-6}/K - 10 \times 10^{-6}/K$.
8. (Previously presented) The semiconductor light-emitting element mounting member according to claim 1 wherein a thermal conductivity of said substrate is at least 80 W/mK.
9. (Previously presented) The semiconductor light-emitting element mounting member according to claim 1 wherein said semiconductor light-emitting element mounting member is a flat submount.
10. (Previously presented) A semiconductor light-emitting device, comprising:
the semiconductor light-emitting element mounting member of claim 1; and
a semiconductor light-emitting element mounted in said semiconductor light-emitting element mounting member.
11. (Previously presented) The semiconductor light-emitting device according to claim 10 wherein the output of said semiconductor light-emitting element is at least 1 W.
12. (Previously presented) The semiconductor light-emitting mounting member according to claim 1 wherein said substrate is an insulative ceramic.

13. (Previously presented) The semiconductor light-emitting mounting member according to claim 12 wherein the insulative ceramic is selected from a group consisting of AlN, Al₂O₃, SiC, Si₃N₄, BeO, BN, and insulative Si.